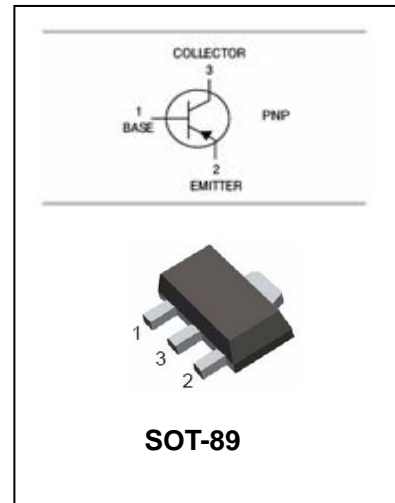


PNP Silicon Epitaxial Planar Transistor

2SB1386

FEATURES

- Low $V_{CE(sat)} = -0.35V$ (Typ.)
($I_C/I_B = -4A/-0.1A$).
- Excellent DC current gain characteristics.
- Complementary: 2SD2098.



APPLICATIONS

- Low frequency transistor.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SB1386	BHP/BHQ/BHR	SOT-89

MAXIMUM RATING @ $T_a = 25^\circ C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	DC	-5
		Pulse	-10
P_C	Collector Dissipation	500	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^\circ C$

PNP Silicon Epitaxial Planar Transistor

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1.0mA, I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20V, I_B = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -500mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -4A, I_B = -0.1A$		-0.35	-1.0	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -50mA$ $f = 100MHz$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -20V, I_E = 0, f = 1MHz$		60		pF

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BHP	BHQ	BHR

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

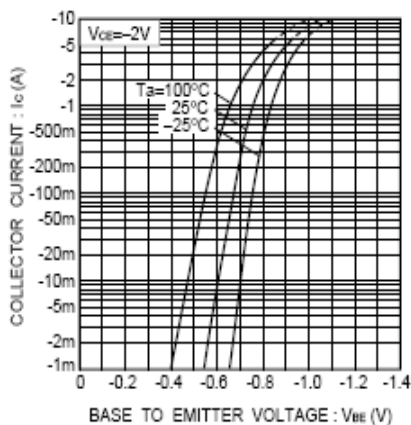


Fig.1 Grounded emitter propagation characteristics

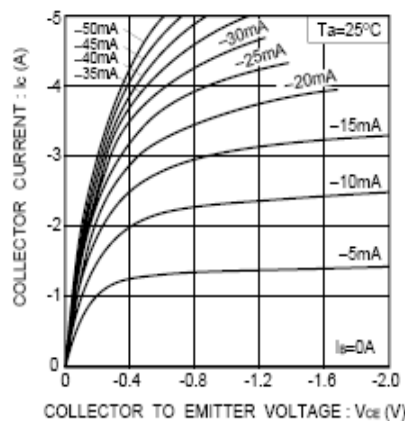


Fig.2 Grounded emitter output characteristics

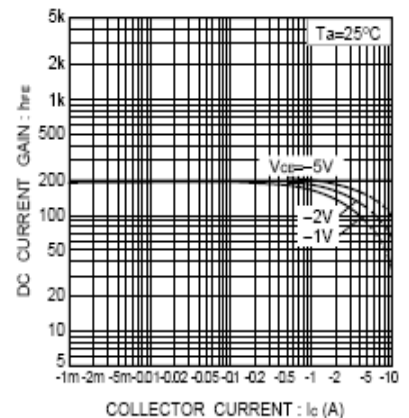


Fig.3 DC current gain vs. collector current (I)

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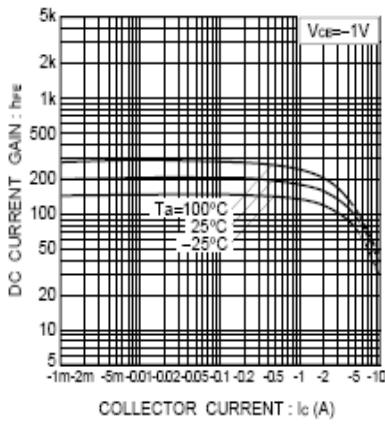


Fig.4 DC current gain vs. collector current (I)

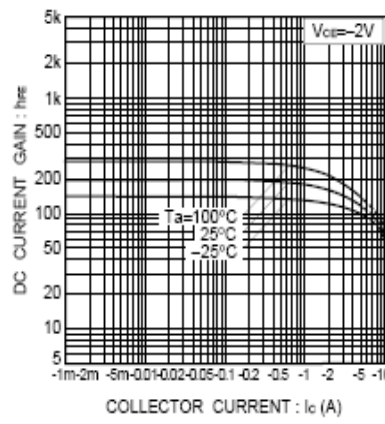


Fig.5 DC current gain vs. collector current (III)

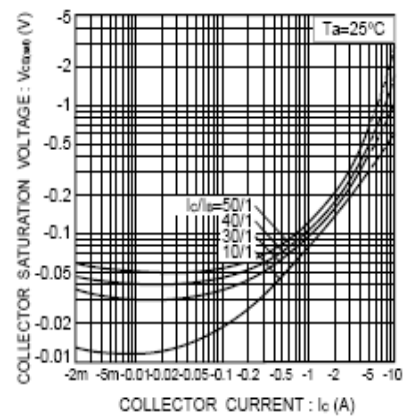


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

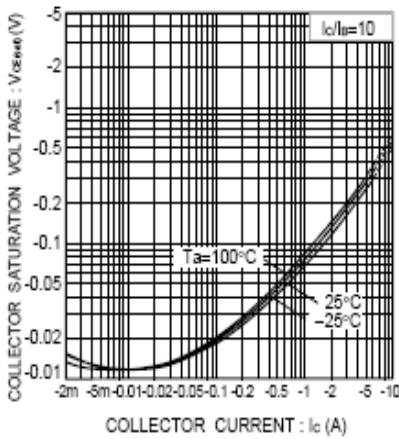


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

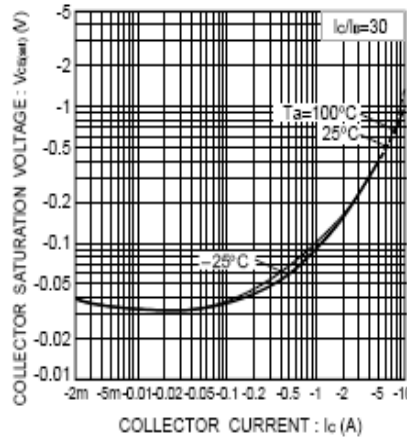


Fig.8 Collector-emitter saturation voltage vs. collector current (III)

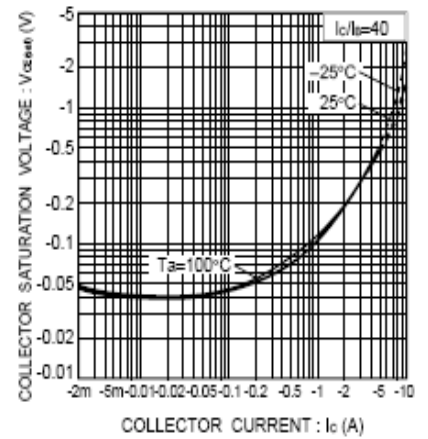


Fig.9 Collector-emitter saturation voltage vs. collector current (IV)

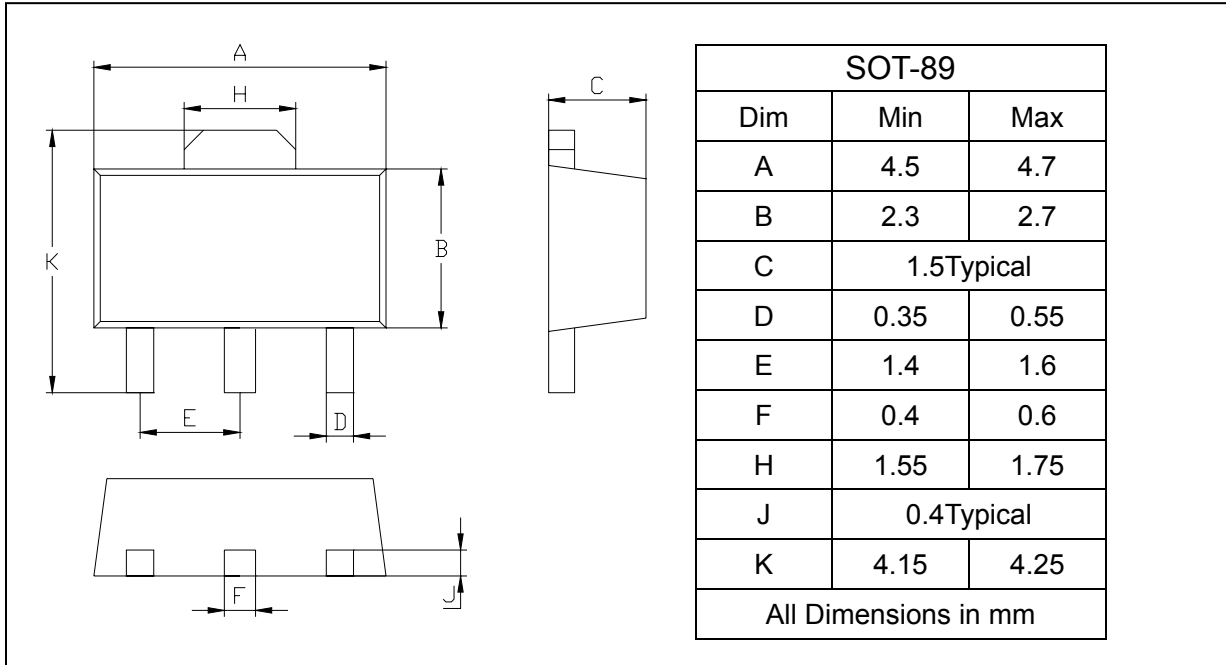
PNP Silicon Epitaxial Planar Transistor

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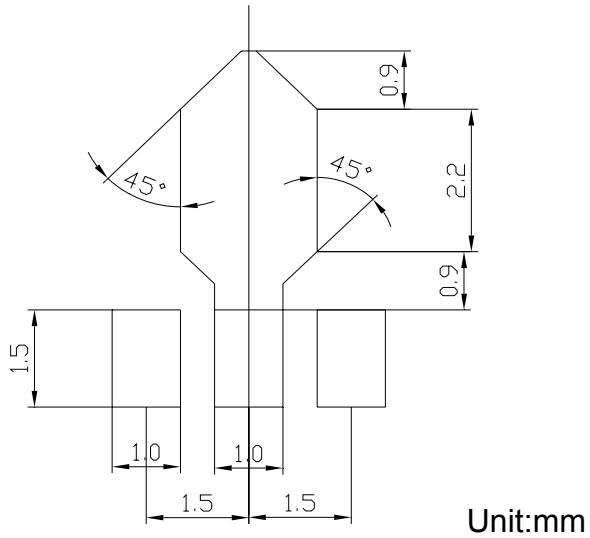
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SB1386	SOT-89	1000/Tape&Reel

www.s-manuals.com